

IGBT3 Power Chip

Features:

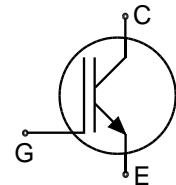
- 1700V Trench & Field stop technology
- low switching losses and saturation losses
- soft turn off
- positive temperature coefficient
- easy paralleling
- Qualified according to JEDEC for target applications

Recommended for:

- power modules

Applications:

- drives



Chip Type	V _{CE}	I _{Cn} ¹⁾	Die Size	Package
IGC136T170S8RH2	1700V	117.5A	17.72 x 7.7 mm ²	sawn on foil

¹⁾ nominal collector current at T_c = 100°C, not subject to production test - verified by design/characterization

Mechanical Parameters

Die size	17.72 x 7.7		mm ²
Emitter pad size (incl. gate pad)	See chip drawing		
Gate pad size	1.674 x 0.899		
Area total	136.4		
Thickness	190		µm
Wafer size	200		mm
Max.possible chips per wafer	187		
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag –system		
Die bond	Electrically conductive epoxy glue and soft solder		
Wire bond	Al, <500µm		
Reject ink dot size	Ø 0.65mm ; max 1.2mm		
Storage environment	for original and sealed MBB bags	Ambient atmosphere air, Temperature 17°C – 25°C, < 6 month	
	for open MBB bags	Acc. to IEC62258-3: Atmosphere >99% Nitrogen or inert gas, Humidity <25%RH, Temperature 17°C – 25°C, < 6 month	



IGC136T170S8RH2

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter voltage, $T_{vj}=25\text{ °C}$	V_{CE}	1700	V
DC collector current, limited by $T_{vj\text{ max}}$	I_C	1)	A
Pulsed collector current, t_p limited by $T_{vj\text{ max}}$ 2)	$I_{C,puls}$	352.5	A
Gate emitter voltage	V_{GE}	± 20	V
Junction temperature range	T_{vj}	-40 ... +175	°C
Operating junction temperature	T_{vj}	-40 ... +150	
Short circuit data 2)3) $V_{GE}=15V, V_{CC}=1000V, T_{vj}=150\text{ °C}$	t_{SC}	10	μs

1) depending on thermal properties of assembly

2) not subject to production test - verified by design/characterization

3) allowed number of short circuits: <1000; time between short circuits: >1s.

Static Characteristics (tested on wafer), $T_{vj}=25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=2\text{ mA}$	1700			V
Collector-Emitter saturation voltage	V_{CEsat}	$V_{GE}=15V, I_C=35.25A$	1.0	1.1	1.3	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C=4.7mA, V_{GE}=V_{CE}$	5.3	5.8	6.3	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1700V, V_{GE}=0V$			7	μA
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$			300	nA
Integrated gate resistor	r_G			11.5		Ω

Electrical Characteristics (not subject to production test - verified by design / characterization)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter saturation voltage	V_{CEsat}	$V_{GE}=15V, I_C=117.5A$		1.75	2.2	V
			$T_{vj}=25\text{ °C}$		2.2	
Input capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25\text{ °C}$		10568		pF
Reverse transfer capacitance	C_{res}			340		